Figures

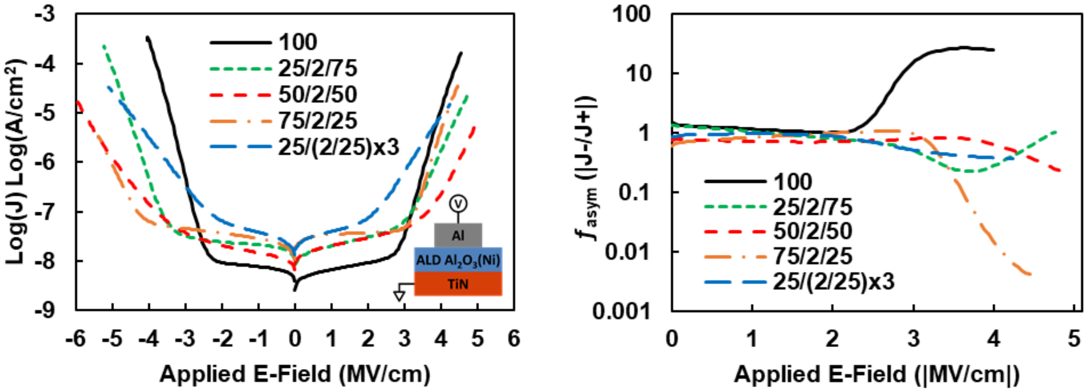

Figure 1. (Left) J-$\mathscr{E}$ sweeps for TiN/Al$_2$O$_3$/Al devices with (dashed lines) and without (black solid line) intentionally placed defects.
Right: f_{asym}-$\mathscr{E}$ curves for TiN/Al$_2$O$_3$/Al devices with (dashed lines) and without (black solid line) intentionally placed defects.

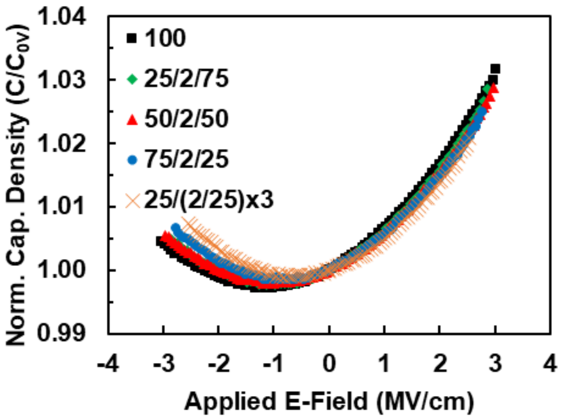

Figure 2. Normalized capacitance density (C/C$_{0V}$) vs. applied electric field for TiN/Al$_2$O$_3$/Al MIM devices with and without intentionally placed defects (as indicated).